Low Capacitance Diode Array for ESD Protection in Two Data Lines

NUP2301MW6T1 is a MicroIntegration[™] device designed to provide protection for sensitive components from possible harmful electrical transients; for example, ESD (electrostatic discharge).

Features

- Low Capacitance (2.0 pf Maximum Between I/O Lines)
- Single Package Integration Design
- Provides ESD Protection for JEDEC Standards JESD22 Machine Model = Class C Human Body Model = Class 3B
- Protection for IEC61000-4-2 (Level 4) 8.0 kV (Contact) 15 kV (Air)
- Ensures Data Line Speed and Integrity
- Fewer Components and Less Board Space
- Direct the Transient to Either Positive Side or to the Ground

Applications

- T1/E1 Secondary IC Protection
- T3/E3 Secondary IC Protection
- HDSL, IDSL Secondary IC Protection
- Video Line Protection
- Microcontroller Input Protection
- Base Stations
- I²C Bus Protection

MAXIMUM RATINGS (Each Diode) ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	Vdc
Forward Current	١ _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc
Repetitive Peak Reverse Voltage	V _{RRM}	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	I _{F(AV)}	715	mA
Repetitive Peak Forward Current	I _{FRM}	450	mA
Non-Repetitive Peak Forward Current t = 1.0 μ s t = 1.0 ms t = 1.0 S	I _{FSM}	2.0 1.0 0.5	A

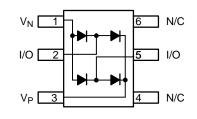
1. FR-5 = 1.0 \times 0.75 \times 0.062 in.



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PIN CONFIGURATION AND SCHEMATIC





MARKING DIAGRAM

SC-88 CASE 419B STYLE 23

68 = Specific Device Code ^d = Date Code

O = Pin 1 Indicator

ORDERING INFORMATION

Device	Package	Shipping
NUP2301MW6T1	SC-88	3000/Tape & Reel

THERMAL CHARACTERISTICS

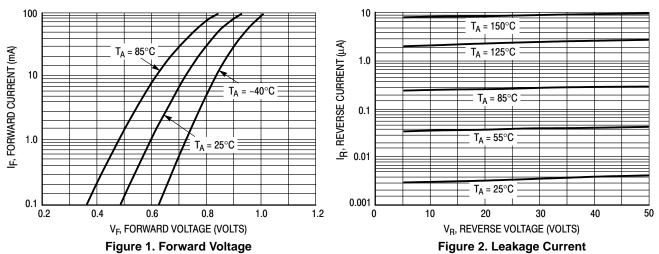
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	625	°C/W
Lead Solder Temperature Maximum 10 Seconds Duration	TL	260	°C
Junction Temperature	TJ	-40 to +85	°C
Storage Temperature	T _{stg}	-55 to +150	°C

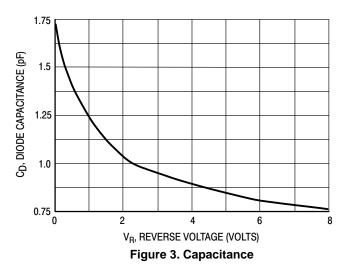
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted) (Each Diode)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μ A	A)	V _(BR)	70	-	-	Vdc
Reverse Voltage Leakage Current	$(V_R = 70 \text{ Vdc})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 70 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I _R	- - -	- -	2.5 30 50	μAdc
Capacitance (between I/O pins)	(V _R = 0 V, f = 1.0 MHz)	CD	-	1.0	2.0	pF
Capacitance (between I/O pin and ground)	(V _R = 0 V, f = 1.0 MHz)	CD	-	1.6	3	pF
Forward Voltage	$(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V _F	- - -		715 855 1000 1250	mV _{dc}

2. FR-5 = 1.0 \times 0.75 \times 0.062 in.

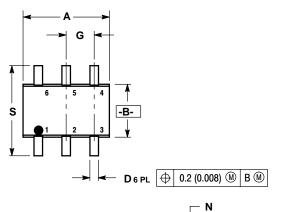
3. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.



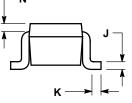


PACKAGE DIMENSIONS

SC-88 (SOT-363) CASE 419B-02 **ISSUE N**



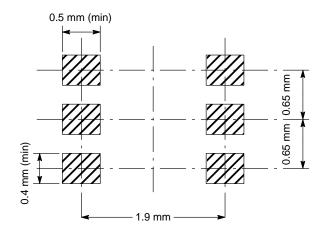
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NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
κ	0.004	0.012	0.10	0.30
Ν	0.008 REF 0.20 RE		REF	
S	0.079	0.087	2.00	2.20

STYLE 23: PIN 1. Vn 2. I/O 3. Vp 4. N/C 5. I/O 6. N/C



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